

*Sub E1*  
*B1*

8. (Amended) An apparatus for processing a semiconductor on a substrate comprising:

an irradiation apparatus for irradiating a linear laser light to said semiconductor therein;

a vacuum apparatus for a vacuum processing; and

a mechanism for transporting said substrate from said vacuum apparatus to said irradiation apparatus without exposing said substrate to outside air.

*Sub E2*  
*B2*

21. (Amended) An apparatus for processing a semiconductor device comprising at least a light processing chamber for treating a [surface] substrate with a linear laser light therein by irradiating said substrate with said linear laser light through a light window provided on a wall of said light processing chamber and an evacuable chamber for performing a vacuum treatment therein, wherein said apparatus is provided with a means for transferring an object from said light processing chamber to said evacuable chamber, or vice versa without exposing said object to air, and wherein said substrate is moved in a direction perpendicularly to said linear laser light in said light processing chamber during the irradiation of said substrate with said linear laser light to crystallize an entire semiconductor film provided on said substrate.

*Sub E3*  
*B3*

27. (Amended) An apparatus for processing a semiconductor device comprising:

a first chamber for treating an object with a linear laser light therein;

a second chamber for treating said object; and

a transferring means for transferring said object from said first chamber to said second chamber without exposing said object to air.

↙ Please cancel claims 16-20.

↙ Please add new claims 41-46 as follows:

*Sub E4*

--41. An apparatus for fabricating a semiconductor device comprising:  
a first chamber for conducting ion doping on a substrate therein; and  
a second chamber for (treating) said substrate with a linear laser light  
therein after said ion doping,

wherein said apparatus is provided with a means for transferring said  
substrate from said first chamber to said second chamber without exposing  
said substrate to air.

*B4*

42. An apparatus for fabricating a semiconductor device comprising:  
a first chamber for conducting plasma doping on a substrate therein;  
and

a second chamber for annealing said substrate with a linear laser light  
therein after said plasma doping,

wherein said apparatus is provided with a means for transferring said  
substrate from said first chamber to said second chamber without exposing  
said substrate to air.

43. An apparatus for fabricating a semiconductor device comprising:  
a first chamber for conducting plasma doping on a substrate therein;  
a second chamber for conducting a dry etching on said substrate  
therein; and

a third chamber for effecting a rapid thermal anneal therein to activate an impurity implanted into said substrate by said plasma doping,

wherein said apparatus is provided with a means for transferring said substrate from one of said first, second and third chambers to another one of said first, second and third chambers without exposing said substrate to air.

*Sub E57*

44. An apparatus for fabricating a semiconductor device comprising:  
a first chamber for conducting plasma chemical vapor deposition on a substrate therein; and

a second chamber for annealing said substrate with a linear laser light therein after said plasma chemical vapor deposition,

wherein said apparatus is provided with a means for transferring said substrate from said first chamber to said second chamber without exposing said substrate to air.

*B4  
cont.*

45. An apparatus for fabricating a semiconductor device comprising:  
a first chamber for treating a substrate with a linear laser light therein;  
and

a second chamber for heating said substrate in hydrogen atmosphere therein after said treating,

wherein said apparatus is provided with a means for transferring said substrate from said first chamber to said second chamber without exposing said substrate to air.

*None Acq'd*

46. An apparatus for fabricating a semiconductor device comprising:  
a first chamber for loading and unloading a substrate; and